Contents of Volume 205

Issue 1

Editorial v

Synthesis and Characterization

Epitaxy of thallium chalcogenide films on ionic crystal surfaces 1
D. I. Ismailov, R. M. Sultanov, F. I. Aliyev and R. B. Shafizade (Baku, U.S.S.R.)

Studies on chemical sputtering of silicon and carbon in Ar–H_2 glow discharge plasma by optical emission spectroscopy. 6
K. Tsuji and K. Hirokawa (Sendai, Japan)

Transmission electron microscopy study of crystallization on plasma-deposited Ge–Se films 13
B Cros (Montpellier, France) , M. Dubourg, J. P. Martinez and J. L. Bailadore (Toulouse, France)

Crystalline particles with multiply twinned structure in amorphous films of germanium 20
H. Hofmeister (Saale, F.R.G.), A. F. Bardamid, T. Junghanns and S. A. Nepijko (Kiev, U.S.S.R.)

Kinetics of vacuum sublimation and condensation of films from the Se–Ag–I system 25
T. Petkova and M. Mitkova (Sofia, Bulgaria)

Growth kinetics of the antimony layer deposited on glass and SiO_x in a vacuum of 10^{-4} Pa 29
H. Mori and M. Hashimoto (Tokyo, Japan)

Surfaces, Interfaces and Colloidal Behaviour

Samarium silicide formation by ultrathin film reaction 35
P. J. Godowski, F. Ørskov, M. Christiansen and J. Onsgaard (Odense, Denmark)

Metallurgical, Protective and Hard Layers

Study on *I–V* characteristics of diamond films synthesized by D.C. arc discharge plasma chemical vapour deposition . . . 39
F. Zhang, W. Zhang, M. Chen, G. Chen (Lanzhou, China) and X. Jiang (Beijing, China)

Study of diamond-like carbon films by secondary ion mass spectrometry 43
M. V. Garcia-Cuenca, C. Serra, F. Lopez and J. L. Morenza (Barcelona, Spain)

W–Re(6 wt.%) and W–Ti(10 wt.%) alloys as diffusion barriers between aluminium and silicon 47
H. Lange, W. Möhling (Berlin, F.R.G.) and G. Marxsen (Erfurt, F.R.G.)

Electronics, Optics and Opto-electronics

Spectral dependence of the absorption coefficient of thin films of non-stoichiometric $Cu_{2-x}Te$ 52
B. S. Farag and S. A. Khodier (Cairo, Egypt)

Investigation of thin dye films on fused silica by optical second harmonic generation 58
L. Werner, F. Marlow, A. Glismann, O. Hertz (Berlin, F.R.G.) and W. Hill (Dortmund, F.R.G.)

Grain boundary scattering in aluminium-doped ZnO films 64
S. Ghosh, A. Sarkar, S. Chaudhuri and A. K. Pal (Calcutta, India)

Modelling the effects of field-dependent quantum efficiency in organic semiconductor Schottky barrier solar cells 69
J. B. Whitlock and P. Panayotatos (Piscataway, NJ, U.S.A.)

Thin ferroelectric films of the lead zirconate-titanate type obtained by r.f. sputtering 76
Z. Surowiak, M. Łoposzko (Sosnowiec, Poland), I. N. Zakharchenko, A. A. Bakirov, E. A. Marchenko, E. V. Sviridov, V. M. Mukhortov and V. P. Dudkevich (Rostov-on-Don, U.S.S.R.)

Electrochromic properties of cesium tungstate with pyrochlore structure 85
Q. Zhong and K. Colbow (Burnaby, B.C., Canada)

Thin film hydrogenated silicon–sulphur alloys as promising materials for solar cell applications 89
S. Al-Dallal, M. Hammam, S. M. Al-Alawi and S. Aljishi (Bahrain, Bahrain)

Physical properties of pyrolytically sprayed tin-doped indium oxide coatings 93
H., Haitjema and J. J. Ph Elich (Delft, The Netherlands)

Chemical processing of thin chromium films 101
I. C. Szép (Budapest, Hungary)

LiF films: absorption and luminescence of colour centres 106
R. M. Montereali, G. Baldacchini (Rome, Italy) and L. C. Scavarda Do Carmo (Rio de Janeiro, Brazil)

Langmuir–Blodgett, Biological and Related Films

Patterning of polyimide precursor Langmuir–Blodgett films and their application as deep UV resists 109
M. Uekita, H. Awaji, M. Murata and S. Mizunuma (Kobe, Japan)

Langmuir–Blodgett films of immunoglobulin G for immunosensors 113
I. V. Turko, I. S. Yirkevich and V. L. Chashchin (Minsk, U.S.S.R.)

Pressure anisotropy and orientational order of a polydiacetylene monolayer and its use as a template for vacuum deposition 117
K. Miyano and T. Hasegawa (Tokyo, Japan)

Contents of Volume 205

Issue 1

Editorial v

Synthesis and Characterization

Epitaxy of thallium chalcogenide films on ionic crystal surfaces 1
D. I. Ismailov, R. M. Sultanov, F. I. Aliyev and R. B. Shafizade (Baku, U.S.S.R.)

Studies on chemical sputtering of silicon and carbon in Ar–H_2 glow discharge plasma by optical emission spectroscopy. 6
K. Tsuji and K. Hirokawa (Sendai, Japan)

Transmission electron microscopy study of crystallization on plasma-deposited Ge–Se films 13
B Cros (Montpellier, France) , M. Dubourg, J. P. Martinez and J. L. Bailadore (Toulouse, France)

Crystalline particles with multiply twinned structure in amorphous films of germanium 20
H. Hofmeister (Saale, F.R.G.), A. F. Bardamid, T. Junghanns and S. A. Nepijko (Kiev, U.S.S.R.)

Kinetics of vacuum sublimation and condensation of films from the Se–Ag–I system 25
T. Petkova and M. Mitkova (Sofia, Bulgaria)

Growth kinetics of the antimony layer deposited on glass and SiO_x in a vacuum of 10^{-4} Pa 29
H. Mori and M. Hashimoto (Tokyo, Japan)

Surfaces, Interfaces and Colloidal Behaviour

Samarium silicide formation by ultrathin film reaction 35
P. J. Godowski, F. Ørskov, M. Christiansen and J. Onsgaard (Odense, Denmark)

Metallurgical, Protective and Hard Layers

Study on *I–V* characteristics of diamond films synthesized by D.C. arc discharge plasma chemical vapour deposition . . . 39
F. Zhang, W. Zhang, M. Chen, G. Chen (Lanzhou, China) and X. Jiang (Beijing, China)

Study of diamond-like carbon films by secondary ion mass spectrometry 43
M. V. Garcia-Cuenca, C. Serra, F. Lopez and J. L. Morenza (Barcelona, Spain)

W–Re(6 wt.%) and W–Ti(10 wt.%) alloys as diffusion barriers between aluminium and silicon 47
H. Lange, W. Möhling (Berlin, F.R.G.) and G. Marxsen (Erfurt, F.R.G.)

Electronics, Optics and Opto-electronics

Spectral dependence of the absorption coefficient of thin films of non-stoichiometric $Cu_{2-x}Te$ 52
B. S. Farag and S. A. Khodier (Cairo, Egypt)

Investigation of thin dye films on fused silica by optical second harmonic generation 58
L. Werner, F. Marlow, A. Glismann, O. Hertz (Berlin, F.R.G.) and W. Hill (Dortmund, F.R.G.)

Grain boundary scattering in aluminium-doped ZnO films 64
S. Ghosh, A. Sarkar, S. Chaudhuri and A. K. Pal (Calcutta, India)

Modelling the effects of field-dependent quantum efficiency in organic semiconductor Schottky barrier solar cells 69
J. B. Whitlock and P. Panayotatos (Piscataway, NJ, U.S.A.)

Thin ferroelectric films of the lead zirconate-titanate type obtained by r.f. sputtering 76
Z. Surowiak, M. Łoposzko (Sosnowiec, Poland), I. N. Zakharchenko, A. A. Bakirov, E. A. Marchenko, E. V. Sviridov, V. M. Mukhortov and V. P. Dudkevich (Rostov-on-Don, U.S.S.R.)

Electrochromic properties of cesium tungstate with pyrochlore structure 85
Q. Zhong and K. Colbow (Burnaby, B.C., Canada)

Thin film hydrogenated silicon–sulphur alloys as promising materials for solar cell applications 89
S. Al-Dallal, M. Hammam, S. M. Al-Alawi and S. Aljishi (Bahrain, Bahrain)

Physical properties of pyrolytically sprayed tin-doped indium oxide coatings 93
H., Haitjema and J. J. Ph Elich (Delft, The Netherlands)

Chemical processing of thin chromium films 101
I. C. Szép (Budapest, Hungary)

LiF films: absorption and luminescence of colour centres 106
R. M. Montereali, G. Baldacchini (Rome, Italy) and L. C. Scavarda Do Carmo (Rio de Janeiro, Brazil)

Langmuir–Blodgett, Biological and Related Films

Patterning of polyimide precursor Langmuir–Blodgett films and their application as deep UV resists 109
M. Uekita, H. Awaji, M. Murata and S. Mizunuma (Kobe, Japan)

Langmuir–Blodgett films of immunoglobulin G for immunosensors 113
I. V. Turko, I. S. Yirkevich and V. L. Chashchin (Minsk, U.S.S.R.)

Pressure anisotropy and orientational order of a polydiacetylene monolayer and its use as a template for vacuum deposition 117
K. Miyano and T. Hasegawa (Tokyo, Japan)

Relationships between fatty acid monolayer stucture on the subphase and on solid substrates. 124
R. Steitz (Mainz, F.R.G.), E. E. Mitchell (North Ryde, NSW, Australia) and I. R. Peterson (Mainz, F.R.G.)

Issue 2

Synthesis and Characterization

Microstructural evolution and properties of nanocrystalline alumina made by reactive sputtering deposition. 131
T. C. Chou, D. Adamson, J. Mardinly and T. G. Nieh (Palo Alto, CA, U.S.A.)
Effects of deposition temperature on properties of r.f. glow discharge amorphous silicon thin films 140
E. Bertran, J. L. Andújar, A. Canillas, C. Roch, J. Serra and G. Sardin (Barcelona, Spain)
Texture and columnar grain structure in obliquely deposited Co–Ni films 146
T. Hashimoto (Tottori, Japan), K. Okamoto (Chiba, Japan), H. Fujiwara (Hiroshima, Japan), K. Itoh, M. Kamiya and K. Hara (Kumamoto, Japan)
Transmission electron microscopy studies of microstructural evolution, defect structure, and phase transitions in polycrystalline and epitaxial $Ti_{1-x}Al_xN$ and TiN films grown by reactive magnetron sputter deposition 153
L. Hultman, G. Håkansson, U. Wahlström, J.-E. Sundgren (Linkoping, Sweden), I. Petrov, F. Adibi and J. E. Greene (Urbana, IL, U.S.A.)
X-ray photoelectron spectroscopy analyses of plasma-deposited $GeSe_x$ films 165
C. Cardinaud, G. Turban (Nantes, France), B. Cros and M. Ribes (Montpellier, France)

Metallurgical, Protective and Hard Layers

Stucture and microhardness of TiN compositional and alloyed films. 171
R. A. Andrievski, I. A. Anisimova (Moscow, U.S.S.R.) and V. P. Anisimov (Bishkek, U.S.R.R.)
Dynamic fracture test of metal thin films deposited on an insulating substrate by a high current pulse method 176
K. Y. Kim and W. Sachse (Ithaca, NY, U.S.A.)

Electronics, Optics and Opto-electronics

Review: Molecular beam epitaxial growth of GaAs and other compound semiconductors 182
K. Adomi, J.-I. Chyi, S. F. Fang, T. C. Shen, S. Strige and H. Morkoç (Urbana, IL, U.S.A.)
New amorphous titanum oxysulfides obtained in the form of thin films 213
G. Meunier, R. Dormoy and A. Levasseur (Talence, France)
The influence of illumination on the time–voltage dependence measured on piezoelectret thin film metal–CdTe–metal structures. 218
D. Valentovič and J. Červenák (Bratislava, Czechoslovakia)
Chemical bonds and spin properties of a-Si_x–Ge_y:H_z alloys. 223
S. Basrour, E. Bustarret and J. C. Bruyère (Grenoble, France)
Effect of pre-oxidation HF treatment on the tunnel oxide (SiO_x) grown at high pressure 227
E. T. P. Benny and J. Majhi (Madras, India)
An attenuated total reflection study of silver film growth 233
D. V. K. Knebel, J. C. Villagran and J. C. Thompson (Austin, TX, U.S.A.)
Ultra-high vacuum metalorganic chemical vapor deposition of GaAs thin films onto Si(100) using a single-source precursor 236
J.-P. Lu, R. Raj (Ithaca, NY, U.S.A.) and A. Wernberg (Rochester, NY, U.S.A.)
Temperature dependence studies of low-frequency capacitance measurements in α- and β-iron phthalocyanines 241
T. G. Abdel-Malik (El-Minia, Egypt)
Effects of wet oxidation on the electrical properties of sub-10 nm thick silicon nitride films. 246
E. G. Lee, J. S. Roh and H. B. Im (Seoul, Korea)
Applications of derivative line-shape fitting to ellipsometric spectra of thin films of metal-substituted phthalocyanines . 257
J. Mårtensson and H. Arwin (Linköping, Sweden)
Depth profiling of layered structures in conducting polymer thin films prepared by the potential-programmed electropolymerization method 258
T. Iyoda, H. Toyoda, M. Fujitsuka, R. Nakahara, K. Honda, T. Shimidzu (Kyoto, Japan), S. Tomita, Y. Hatano, F. Soeda and A. Ishitani (Shiga, Japan)
Characteristics of rapidly thermally annealed RuO_2 films on SiO_2 266
T. S. Kalkur (Colorado Springs, CO, U.S.A.) and Y. C. Lu (Piscataway, NJ, U.S.A.)

Thin Film Devices, Sensors and Actuators

Thermochromic and photoluminescent properties in Langmuir–Blodgett multilayer thin films containing poly(3-dodecylthiophene) 270
I. Watanabe (Ibaraki, Japan) and T. Shimidzu (Kyoto, Japan)

Condensed Matter Film Behaviour

Characterization of the sp^2 bonds network in a-C:H layers with nuclear magnetic resonance, electron energy loss spectroscopy and electron spin resonance 274
R. Kleber, K. Jung, H. Ehrhardt (Kaiserslautern, F.R.G.), I. Mühling, K. Breuer (Chemnitz, F.R.G.), H. Metz and F. Engelke (Leipzig, F.R.G.)